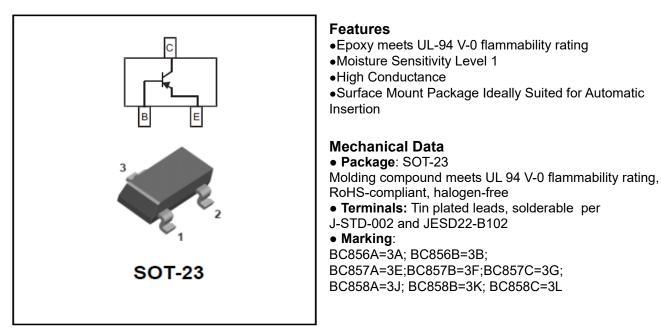
PNP Transistor



■ Maximum Ratings (Ta=25 °C unless otherwise noted)

Symbol	Parameter	Value	Unit
ВУсво	Collector-Base Voltage BC856 BC857 BC858	-80 -50 -30	V
BVCEO	Collector-Emitter Voltage BC856 BC857 BC858	-65 -45 -30	V
ВУево	Emitter-Base Voltage	-6	V
IC	Collector Current –Continuous	-0.1	А
Pc	Collector Power Dissipation	200	mW
Roja	Thermal Resistance From Junction To Ambient	625	°C/W
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~+150	°C





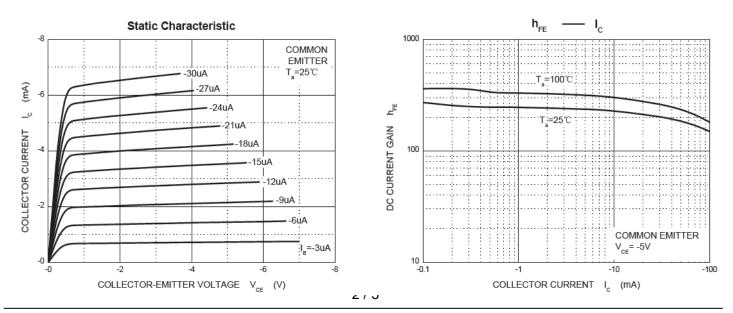
■ Electrical Characteristics (Ta=25°C unless otherwise noted)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage BC856 BC857 BC858	BVCBO	IC= -10μΑ, IE=0	-80 -50 -30		V
Collector-emitter breakdown voltage BC856 BC857 BC858	BVCEO	IC= -10mA, IB=0	-65 -45 -30		V
Emitter-base breakdown voltage	BVEBO	IE= -1μΑ, IC=0	-5		V
Collector cut-off current	ICBO	VCB=-30 V ,IE=0		-0.1	μA
Emitter cut-off current	IEBO	VEB=-5 V , IC=0		-0.1	μA
DC current gain BC856A,857A,858A BC856B,857B,858B BC857C,BC858C	hFE	VCE= -5V, IC= -2mA	125 220 420	250 475 800	
Collector-emitter saturation voltage	VCE(sat)	IC=-100mA, IB= -5mA		-0.65	V
Base-emitter saturation voltage	VBE(sat)	IC=-100mA, IB= -5mA		-1.1	V
Transition frequency	fT	VCE= -5 V, IC= -10mA f=100MHz	100		MHz
Collector output capacitance	Cob	VCB=-10V,f=1MHz		4.5	pF

Ordering Information (Example)

PREFERED P/N	PACKING CODE	UNIT WEIGHT(g)	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
BC856/BC857/BC858	F2	Approximate 0.008	3000	30000	120000	7" reel

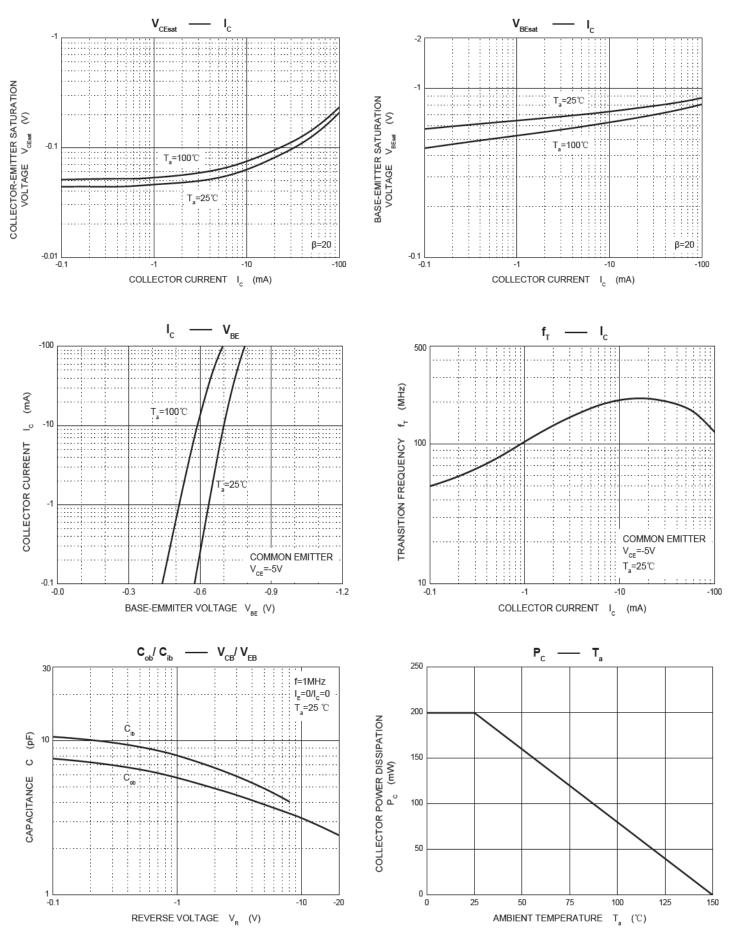
Characteristics(Typical)



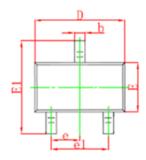


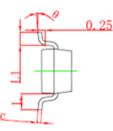
BC856/BC857/BC858

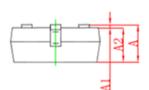




■SOT-23 Package Outline Dimensions

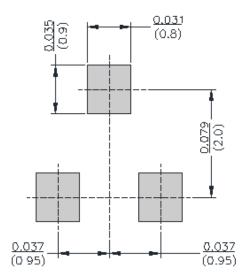






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
A	0.900	1.150	0.035	0.045	
Al	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
c	0.100	0.200	0.004	0.008	
D	2.800	3.000	0.110	0.118	
Е	1.200	1. 400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
e	0. 950TYP		0. 037TYP		
el	1.800	2.000	0.071	0.079	
L	0. 550REF		0. 022REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8*	

■SOT-23Suggested Pad Layout



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